

P- Channel Enhancement-Mode Vertical DMOS FETs, MOSFET 400V 150hm

Manufacturers	Microchip Technology, Inc
Package/Case	SOIC-8
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for TP2640LG-G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown. Vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Features

Low threshold (-2.0V max.)

High input impedance

Low input capacitance

Fast switching speeds

Low on-resistance

Free from secondary breakdown

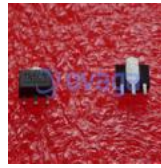
Low input and output leakage

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